WHAT IS CLAIMED IS:

1. A method for cleaning a semiconductor manufacturing system having multiple sections of tubes, the method comprising acts of:

opening one of the multiple sections of tubes in the system;

introducing a high purity and highly volatile cleaning agent into the optional one of the multiple sections of tubes;

washing the optional section of tubes with the high purity and highly volatile cleaning agent; and

drying the optional section of tubes;

wherein, the method uses the high purity and highly volatile cleaning agent in form of liquid to wash the system and is adapted to dissolve and wash out chemicals used in the system.

2. The method as claimed in claim 1, wherein a purge gas is introduced into the system to purge the system before introducing the high purity and highly volatile cleaning agent.

3. The method as claimed in claim 1, wherein a purge gas is introduced into the system at the same time of introducing the high purity and highly volatile cleaning agent.

4. The method as claimed in claim 1, wherein a system pressurization gas is introduced into the system after introducing the high purity and highly volatile cleaning agent.

5. The method as claimed in claim 2, wherein a system pressurization gas is introduced into the system after introducing the high purity and highly volatile cleaning agent.

6. The method as claimed in claim 3, wherein a system pressurization gas is introduced into the system after introducing the high purity and highly volatile cleaning agent.

7. The method as claimed in claim 5, wherein the purging agent is selected from the group comprising hexane, acetone, iso-propanol and toluene.

8. The method as claimed in claim 7, wherein the purge gas is nitrogen.

9. The method as claimed in claim 8, wherein the system pressurization gas is selected from the group comprising helium and nitrogen.

10. The method as claimed in claim 9, wherein the purge gas and the system pressurization gas are heated to speed up cleaning of the system.